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Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Active
Core Processor	PIC
Core Size	8-Bit
Speed	20MHz
Connectivity	-
Peripherals	Brown-out Detect/Reset, POR, PWM, WDT
Number of I/O	5
Program Memory Size	1.75KB (1K x 14)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	64 x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 5.5V
Data Converters	A/D 4x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	8-SOIC (0.154", 3.90mm Width)
Supplier Device Package	8-SOIC
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/pic12f615-i-sn

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

1.0 DEVICE OVERVIEW

The PIC12F609/615/617/12HV609/615 devices are covered by this data sheet. They are available in 8-pin PDIP, SOIC, MSOP and DFN packages.

Block Diagrams and pinout descriptions of the devices are as follows:

- PIC12F609/HV609 (Figure 1-1, Table 1-1)
- PIC12F615/617/HV615 (Figure 1-2, Table 1-2)





3.0 FLASH PROGRAM MEMORY SELF READ/SELF WRITE CONTROL (FOR PIC12F617 ONLY)

The Flash program memory is readable and writable during normal operation (full VDD range). This memory is not directly mapped in the register file space. Instead, it is indirectly addressed through the Special Function Registers (see Registers 3-1 to 3-5). There are six SFRs used to read and write this memory:

- PMCON1
- PMCON2
- PMDATL
- PMDATH
- PMADRL
- PMADRH

When interfacing the program memory block, the PMDATL and PMDATH registers form a two-byte word which holds the 14-bit data for read/write, and the PMADRL and PMADRH registers form a two-byte word which holds the 13-bit address of the Flash location being accessed. These devices have 2K words of program Flash with an address range from 0000h to 07FFh.

The program memory allows single word read and a by four word write. A four word write automatically erases the row of the location and writes the new data (erase before write).

The write time is controlled by an on-chip timer. The write/erase voltages are generated by an on-chip charge pump rated to operate over the voltage range of the device for byte or word operations.

When the device is code-protected, the CPU may continue to read and write the Flash program memory.

Depending on the settings of the Flash Program Memory Enable (WRT<1:0>) bits, the device may or may not be able to write certain blocks of the program memory, however, reads of the program memory are allowed.

When the Flash program memory Code Protection (\overline{CP}) bit in the Configuration Word register is enabled, the program memory is code-protected, and the device programmer (ICSPTM) cannot access data or program memory.

3.1 PMADRH and PMADRL Registers

The PMADRH and PMADRL registers can address up to a maximum of 8K words of program memory.

When selecting a program address value, the Most Significant Byte (MSB) of the address is written to the PMADRH register and the Least Significant Byte (LSB) is written to the PMADRL register.

3.2 PMCON1 and PMCON2 Registers

PMCON1 is the control register for the data program memory accesses.

Control bits RD and WR initiate read and write, respectively. These bits cannot be cleared, only set in software. They are cleared in hardware at completion of the read or write operation. The inability to clear the WR bit in software prevents the accidental premature termination of a write operation.

The WREN bit, when set, will allow a write operation. On power-up, the WREN bit is clear.

PMCON2 is not a physical register. Reading PMCON2 will read all '0's. The PMCON2 register is used exclusively in the Flash memory write sequence.

REGISTER 5-2: TRISIO: GPIO TRI-STATE REGISTER

U-0	U-0	R/W-1	R/W-1	R-1	R/W-1	R/W-1	R/W-1	
—	—	TRISIO5	TRISIO4	TRISIO3	TRISIO2	TRISIO1	TRISIO0	
bit 7							bit 0	
Legend:								
R = Readable bit W = Writable bit			it	U = Unimplemented bit, read as '0'				
-n = Value at POR '1' = Bit is set				0' = Bit is cleared $x = Bit is unknown$				

bit 7-6 Unimplemented: Read as '0'

TRISIO<5:0>: GPIO Tri-State Control bit

1 = GPIO pin configured as an input (tri-stated)

0 = GPIO pin configured as an output

Note 1: TRISIO<3> always reads '1'.

bit 5-0

2: TRISIO<5:4> always reads '1' in XT, HS and LP Oscillator modes.

5.2 Additional Pin Functions

Every GPIO pin on the PIC12F609/615/617/12HV609/ 615 has an interrupt-on-change option and a weak pullup option. The next three sections describe these functions.

5.2.1 ANSEL REGISTER

The ANSEL register is used to configure the Input mode of an I/O pin to analog. Setting the appropriate ANSEL bit high will cause all digital reads on the pin to be read as '0' and allow analog functions on the pin to operate correctly.

The state of the ANSEL bits has no affect on digital output functions. A pin with TRIS clear and ANSEL set will still operate as a digital output, but the Input mode will be analog. This can cause unexpected behavior when executing read-modify-write instructions on the affected port.

5.2.2 WEAK PULL-UPS

Each of the GPIO pins, except GP3, has an individually configurable internal weak pull-up. Control bits WPUx enable or disable each pull-up. Refer to Register 5-5. Each weak pull-up is automatically turned off when the port pin is configured as an output. The pull-ups are disabled on a Power-on Reset by the GPPU bit of the OPTION register). A weak pull-up is automatically enabled for GP3 when configured as MCLR and disabled when GP3 is an I/O. There is no software control of the MCLR pull-up.

5.2.3 INTERRUPT-ON-CHANGE

Each GPIO pin is individually configurable as an interrupt-on-change pin. Control bits IOCx enable or disable the interrupt function for each pin. Refer to Register 5-6. The interrupt-on-change is disabled on a Power-on Reset.

For enabled interrupt-on-change pins, the values are compared with the old value latched on the last read of GPIO. The 'mismatch' outputs of the last read are OR'd together to set the GPIO Change Interrupt Flag bit (GPIF) in the INTCON register (Register 2-3).

This interrupt can wake the device from Sleep. The user, in the Interrupt Service Routine, clears the interrupt by:

- Any read of GPIO AND Clear flag bit GPIF. This will end the mismatch condition;
 OR
- b) Any write of GPIO AND Clear flag bit GPIF will end the mismatch condition;

A mismatch condition will continue to set flag bit GPIF. Reading GPIO will end the mismatch condition and allow flag bit GPIF to be cleared. The latch holding the last read value is not affected by a MCLR nor BOR Reset. After these resets, the GPIF flag will continue to be set if a mismatch is present.

Note:	If a change on the I/O pin should occur							
	when any GPIO operation is being							
	executed, then the GPIF interrupt flag may							
	not get set.							

7.0 TIMER1 MODULE WITH GATE CONTROL

The Timer1 module is a 16-bit timer/counter with the following features:

- 16-bit timer/counter register pair (TMR1H:TMR1L)
- Programmable internal or external clock source
- 3-bit prescaler
- Optional LP oscillator
- Synchronous or asynchronous operation
- Timer1 gate (count enable) via comparator or $\overline{\text{T1G}}$ pin
- Interrupt on overflow
- Wake-up on overflow (external clock, Asynchronous mode only)
- Time base for the Capture/Compare function
- Special Event Trigger (with ECCP)
- Comparator output synchronization to Timer1 clock

Figure 7-1 is a block diagram of the Timer1 module.

7.1 Timer1 Operation

The Timer1 module is a 16-bit incrementing counter which is accessed through the TMR1H:TMR1L register pair. Writes to TMR1H or TMR1L directly update the counter.

When used with an internal clock source, the module is a timer. When used with an external clock source, the module can be used as either a timer or counter.

7.2 Clock Source Selection

The TMR1CS bit of the T1CON register is used to select the clock source. When TMR1CS = 0, the clock source is FOSC/4. When TMR1CS = 1, the clock source is supplied externally.

Clock Source	TMR1CS	T1ACS
Fosc/4	0	0
Fosc	0	1
T1CKI pin	1	x

7.10 **ECCP Special Event Trigger** (PIC12F615/617/HV615 only)

If a ECCP is configured to trigger a special event, the trigger will clear the TMR1H:TMR1L register pair. This special event does not cause a Timer1 interrupt. The ECCP module may still be configured to generate a ECCP interrupt.

In this mode of operation, the CCPR1H:CCPR1L register pair effectively becomes the period register for Timer1.

Timer1 should be synchronized to the Fosc to utilize the Special Event Trigger. Asynchronous operation of Timer1 can cause a Special Event Trigger to be missed.

In the event that a write to TMR1H or TMR1L coincides with a Special Event Trigger from the ECCP, the write will take precedence.

For more information, see Section 11.0 "Enhanced Capture/Compare/PWM (With Auto-Shutdown and Dead Band) Module (PIC12F615/617/HV615 only)".

7.11 **Comparator Synchronization**

The same clock used to increment Timer1 can also be used to synchronize the comparator output. This feature is enabled in the Comparator module.

When using the comparator for Timer1 gate, the comparator output should be synchronized to Timer1. This ensures Timer1 does not miss an increment if the comparator changes.

For more information, see Section 9.0 "Comparator Module".



9.5 Comparator Interrupt Operation

The comparator interrupt flag can be set whenever there is a change in the output value of the comparator. Changes are recognized by means of a mismatch circuit which consists of two latches and an exclusiveor gate (see Figure 9-4 and Figure 9-5). One latch is updated with the comparator output level when the CMCON0 register is read. This latch retains the value until the next read of the CMCON0 register or the occurrence of a Reset. The other latch of the mismatch circuit is updated on every Q1 system clock. A mismatch condition will occur when a comparator output change is clocked through the second latch on the Q1 clock cycle. At this point the two mismatch latches have opposite output levels which is detected by the exclusive-or gate and fed to the interrupt circuitry. The mismatch condition persists until either the CMCON0 register is read or the comparator output returns to the previous state.

- **Note 1:** A write operation to the CMCON0 register will also clear the mismatch condition because all writes include a read operation at the beginning of the write cycle.
 - 2: Comparator interrupts will operate correctly regardless of the state of CMOE.

The comparator interrupt is set by the mismatch edge and not the mismatch level. This means that the interrupt flag can be reset without the additional step of reading or writing the CMCON0 register to clear the mismatch registers. When the mismatch registers are cleared, an interrupt will occur upon the comparator's return to the previous state, otherwise no interrupt will be generated.

Software will need to maintain information about the status of the comparator output, as read from the CMCON1 register, to determine the actual change that has occurred.

The CMIF bit of the PIR1 register is the Comparator Interrupt flag. This bit must be reset in software by clearing it to '0'. Since it is also possible to write a '1' to this register, an interrupt can be generated.

The CMIE bit of the PIE1 register and the PEIE and GIE bits of the INTCON register must all be set to enable comparator interrupts. If any of these bits are cleared, the interrupt is not enabled, although the CMIF bit of the PIR1 register will still be set if an interrupt condition occurs.





COMPARATOR INTERRUPT TIMING WITH CMCON0 READ



- Note 1: If a change in the CMCON0 register (COUT) should occur when a read operation is being executed (start of the Q2 cycle), then the CMIF of the PIR1 register interrupt flag may not get set.
 - 2: When a comparator is first enabled, bias circuitry in the comparator module may cause an invalid output from the comparator until the bias circuitry is stable. Allow about 1 μs for bias settling then clear the mismatch condition and interrupt flags before enabling comparator interrupts.

TABLE 10-1: ADC CLOCK PERIOD (TAD) Vs. DEVICE OPERATING FREQUENCIES (VDD > 3.0V)

ADC Clock	Period (TAD)	Device Frequency (Fosc)					
ADC Clock Source	ADCS<2:0>	20 MHz	8 MHz	4 MHz	1 MHz		
Fosc/2	000	100 ns ⁽²⁾	250 ns ⁽²⁾	500 ns ⁽²⁾	2.0 μs		
Fosc/4	100	200 ns ⁽²⁾	500 ns ⁽²⁾	1.0 μs ⁽²⁾	4.0 μs		
Fosc/8	001	400 ns ⁽²⁾	1.0 μs (2)	2.0 μs	8.0 μs ⁽³⁾		
Fosc/16	101	800 ns ⁽²⁾	2.0 μs	4.0 μs	16.0 μs ⁽³⁾		
Fosc/32	010	1.6 μs	4.0 μs	8.0 μs ⁽³⁾	32.0 μs ⁽³⁾		
Fosc/64	110	3.2 μs	8.0 μs ⁽³⁾	16.0 μs ⁽³⁾	64.0 μs ⁽³⁾		
FRC	x11	2-6 μs ^(1,4)	2-6 μs ^(1,4)	2-6 μs ^(1,4)	2-6 μs ^(1,4)		

Legend: Shaded cells are outside of recommended range.

- **Note 1:** The FRC source has a typical TAD time of 4 μ s for VDD > 3.0V.
 - 2: These values violate the minimum required TAD time.
 - 3: For faster conversion times, the selection of another clock source is recommended.
 - 4: When the device frequency is greater than 1 MHz, the FRC clock source is only recommended if the conversion will be performed during Sleep.

FIGURE 10-2: ANALOG-TO-DIGITAL CONVERSION TAD CYCLES



10.1.5 INTERRUPTS

The ADC module allows for the ability to generate an interrupt upon completion of an Analog-to-Digital conversion. The ADC interrupt flag is the ADIF bit in the PIR1 register. The ADC interrupt enable is the ADIE bit in the PIE1 register. The ADIF bit must be cleared in software.

Note:	The ADIF bit is set at the completion of						
	every conversion, regardless of whether						
	or not the ADC interrupt is enabled.						

This interrupt can be generated while the device is operating or while in Sleep. If the device is in Sleep, the interrupt will wake-up the device. Upon waking from Sleep, the next instruction following the SLEEP instruction is always executed. If the user is attempting to wake-up from Sleep and resume in-line code execution, the global interrupt must be disabled. If the global interrupt is enabled, execution will switch to the Interrupt Service Routine.

Please see **Section 10.1.5** "Interrupts" for more information.

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10.3 A/D Acquisition Requirements

For the ADC to meet its specified accuracy, the charge holding capacitor (CHOLD) must be allowed to fully charge to the input channel voltage level. The Analog Input model is shown in Figure 10-4. The source impedance (Rs) and the internal sampling switch (Rss) impedance directly affect the time required to charge the capacitor CHOLD. The sampling switch (Rss) impedance varies over the device voltage (VDD), see Figure 10-4. **The maximum recommended impedance for analog sources is 10 k** Ω . As the source impedance is decreased, the acquisition time may be decreased. After the analog input channel is selected (or changed), an A/D acquisition must be done before the conversion can be started. To calculate the minimum acquisition time, Equation 10-1 may be used. This equation assumes that 1/2 LSb error is used (1024 steps for the ADC). The 1/2 LSb error is the maximum error allowed for the ADC to meet its specified resolution.

EQUATION 10-1: ACQUISITION TIME EXAMPLE

Assumptions: Temperature =
$$50^{\circ}C$$
 and external impedance of $10k\Omega 5.0V$ VDD
 $TACQ = Amplifier Settling Time + Hold Capacitor Charging Time + Temperature Coefficient$
 $= TAMP + TC + TCOFF$

$$= 2\mu s + TC + [(Temperature - 25^{\circ}C)(0.05\mu s/^{\circ}C)]$$

The value for TC can be approximated with the following equations:

$$V_{APPLIED}\left(1 - \frac{1}{2047}\right) = V_{CHOLD} \qquad ;[1] V_{CHOLD} charged to within 1/2 lsb$$

$$V_{APPLIED}\left(1 - e^{\frac{-T_{C}}{R_{C}}}\right) = V_{CHOLD} \qquad ;[2] V_{CHOLD} charge response to V_{APPLIED}$$

$$V_{APPLIED}\left(1-e^{\frac{-1}{RC}}\right) = V_{APPLIED}\left(1-\frac{1}{2047}\right) \quad (combining [1] and [2])$$

Solving for TC:

$$Tc = -C_{HOLD}(R_{IC} + R_{SS} + R_{S}) \ln(1/2047)$$
$$= -10pF(1k\Omega + 7k\Omega + 10k\Omega) \ln(0.0004885)$$
$$= 1.37us$$

Therefore:

$$TACQ = 2\mu s + 1.37\mu s + [(50^{\circ}C - 25^{\circ}C)(0.05\mu s/^{\circ}C)]$$

= 4.67\mu s

Note 1: The reference voltage (VREF) has no effect on the equation, since it cancels itself out.

- 2: The charge holding capacitor (CHOLD) is not discharged after each conversion.
- **3:** The maximum recommended impedance for analog sources is $10 \text{ k}\Omega$. This is required to meet the pin leakage specification.







11.4 PWM (Enhanced Mode)

The Enhanced PWM Mode can generate a PWM signal on up to four different output pins with up to 10-bits of resolution. It can do this through four different PWM output modes:

- Single PWM
- Half-Bridge PWM

To select an Enhanced PWM mode, the P1M bits of the CCP1CON register must be set appropriately.

The PWM outputs are multiplexed with I/O pins and are designated P1A and P1B. The polarity of the PWM pins is configurable and is selected by setting the CCP1M bits in the CCP1CON register appropriately.

Table 11-6 shows the pin assignments for each Enhanced PWM mode.

Figure 11-5 shows an example of a simplified block diagram of the Enhanced PWM module.

Note: To prevent the generation of an incomplete waveform when the PWM is first enabled, the ECCP module waits until the start of a new PWM period before generating a PWM signal.

FIGURE 11-5: EXAMPLE SIMPLIFIED BLOCK DIAGRAM OF THE ENHANCED PWM MODE



Note 1: The TRIS register value for each PWM output must be configured appropriately.

- 2: Clearing the CCP1CON register will relinquish ECCP control of all PWM output pins.
- **3:** Any pin not used by an Enhanced PWM mode is available for alternate pin functions.

TABLE 11-6: EXAMPLE PIN ASSIGNMENTS FOR VARIOUS PWM ENHANCED MODES

ECCP Mode	P1M<1:0>	CCP1/P1A	P1B
Single	00	Yes ⁽¹⁾	Yes ⁽¹⁾
Half-Bridge	10	Yes	Yes

11.4.4 ENHANCED PWM AUTO-SHUTDOWN MODE

The PWM mode supports an Auto-Shutdown mode that will disable the PWM outputs when an external shutdown event occurs. Auto-Shutdown mode places the PWM output pins into a predetermined state. This mode is used to help prevent the PWM from damaging the application.

The auto-shutdown sources are selected using the ECCPASx bits of the ECCPAS register. A shutdown event may be generated by:

- A logic '0' on the INT pin
- Comparator
- Setting the ECCPASE bit in firmware

A shutdown condition is indicated by the ECCPASE (Auto-Shutdown Event Status) bit of the ECCPAS register. If the bit is a '0', the PWM pins are operating normally. If the bit is a '1', the PWM outputs are in the shutdown state. Refer to Figure 1.

When a shutdown event occurs, two things happen:

The ECCPASE bit is set to '1'. The ECCPASE will remain set until cleared in firmware or an auto-restart occurs (see Section 11.4.5 "Auto-Restart Mode").

The enabled PWM pins are asynchronously placed in their shutdown states. The state of P1A is determined by the PSSAC bit. The state of P1B is determined by the PSSBD bit. The PSSAC and PSSBD bits are located in the ECCPAS register. Each pin may be placed into one of three states:

- Drive logic '1'
- Drive logic '0'
- Tri-state (high-impedance)

ECCPAS<2:0> 111 110 101 100 011 010 ╧ PSSAC<0: From Comparator 001 P1A_DRV 000 PRSEN Ŧ PSSAC<1> Х R s TRISx From Data Bus ECCPASE D Q Write to ECCPASE PSSBD<0> P1B DRV PSSBD<1> Х P1B TRIS

FIGURE 11-10: AUTO-SHUTDOWN BLOCK DIAGRAM

16.8 DC Characteristics: PIC12F609/615/617/12HV609/615-I (Industrial) PIC12F609/615/617/12HV609/615-E (Extended) (Continued)

DC CHARACTERISTICS			Standard Operat Operating temper	Depending Conditions (unless otherwise stated)emperature $-40^{\circ}C \le TA \le +85^{\circ}C$ for industrial $-40^{\circ}C \le TA \le +125^{\circ}C$ for extended			
Param No.	Sym	Characteristic	Min Typ† Max Un			Units	Conditions
D101*	COSC2	Capacitive Loading Specs on Output Pins OSC2 pin	_	_	15	pF	In XT, HS and LP modes when external clock is used to drive OSC1
D101A*	Сю	All I/O pins	—	—	50	pF	
		Program Flash Memory					
D130	Eр	Cell Endurance	10K	100K	—	E/W	$-40^{\circ}C \le TA \le +85^{\circ}C$
D130A	ED	Cell Endurance	1K	10K	—	E/W	$+85^{\circ}C \le TA \le +125^{\circ}C$
D131	Vpr	VDD for Read	VMIN	-	5.5	V	Vмın = Minimum operating voltage
D132	VPEW	VDD for Bulk Erase/Write	4.5	—	5.5	V	
D132A	VPEW	VDD for Row Erase/Write ⁽⁶⁾	VMIN	—	5.5	V	
D133	TPEW	Erase/Write cycle time	—	2	2.5	ms	
D134	Tretd	Characteristic Retention	40	_	_	Year	Provided no other specifications are violated

* These parameters are characterized but not tested.

† Data in "Typ" column is at 5.0V, 25°C unless otherwise stated. These parameters are for design guidance only and are not tested.

Note 1: In RC oscillator configuration, the OSC1/CLKIN pin is a Schmitt Trigger input. It is not recommended to use an external clock in RC mode.

2: Negative current is defined as current sourced by the pin.

3: The leakage current on the MCLR pin is strongly dependent on the applied voltage level. The specified levels represent normal operating conditions. Higher leakage current may be measured at different input voltages.

4: This specification applies to GP3/MCLR configured as GP3 with the internal weak pull-up disabled.

5: This specification applies to all weak pull-up pins, including the weak pull-up found on GP3/MCLR. When GP3/MCLR is configured as MCLR reset pin, the weak pull-up is always enabled.

6: Applies to PIC12F617 only.

16.10 Timing Parameter Symbology

The timing parameter symbols have been created with one of the following formats:

- 1. TppS2ppS
- 2. TppS

т			
F	Frequency	Т	Time
Lowerc	ase letters (pp) and their meanings:		
рр			
сс	CCP1	osc	OSC1
ck	CLKOUT	rd	RD
CS	CS	rw	RD or WR
di	SDI	sc	SCK
do	SDO	SS	SS
dt	Data in	tO	TOCKI
io	I/O Port	t1	T1CKI
mc	MCLR	wr	WR
Upperc	ase letters and their meanings:		
S			
F	Fall	Р	Period
Н	High	R	Rise
I	Invalid (High-impedance)	V	Valid
L	Low	Z	High-impedance

FIGURE 16-3: LOAD CONDITIONS



16.11 AC Characteristics: PIC12F609/615/617/12HV609/615 (Industrial, Extended)



FIGURE 16-4: CLOCK TIMING

TABLE 16-1: CLOCK OSCILLATOR TIMING REQUIREMENTS

Standard Operating Conditions (unless otherwise stated)Operating temperature $-40^{\circ}C \le TA \le +125^{\circ}C$									
Param No.	Sym	Characteristic	Min	Тур†	Max	Units	Conditions		
OS01	Fosc	External CLKIN Frequency ⁽¹⁾	DC	_	37	kHz	LP Oscillator mode		
			DC	—	4	MHz	XT Oscillator mode		
			DC	—	20	MHz	HS Oscillator mode		
			DC	—	20	MHz	EC Oscillator mode		
		Oscillator Frequency ⁽¹⁾	_	32.768	_	kHz	LP Oscillator mode		
			0.1	—	4	MHz	XT Oscillator mode		
			1	—	20	MHz	HS Oscillator mode		
			DC	_	4	MHz	RC Oscillator mode		
OS02	Tosc	External CLKIN Period ⁽¹⁾	27		8	μS	LP Oscillator mode		
			250	—	×	ns	XT Oscillator mode		
			50	—	×	ns	HS Oscillator mode		
			50	—	x	ns	EC Oscillator mode		
		Oscillator Period ⁽¹⁾	_	30.5	_	μS	LP Oscillator mode		
			250	—	10,000	ns	XT Oscillator mode		
			50	—	1,000	ns	HS Oscillator mode		
			250	—	—	ns	RC Oscillator mode		
OS03	Тсү	Instruction Cycle Time ⁽¹⁾	200	Тсү	DC	ns	TCY = 4/FOSC		
OS04*	TosH,	External CLKIN High,	2	—	_	μS	LP oscillator		
	TosL	External CLKIN Low	100	—	—	ns	XT oscillator		
			20	—	—	ns	HS oscillator		
OS05*	TosR,	External CLKIN Rise,	0	—	8	ns	LP oscillator		
	TosF	External CLKIN Fall	0	—	×	ns	XT oscillator		
			0	—	×	ns	HS oscillator		

* These parameters are characterized but not tested.

† Data in "Typ" column is at 5V, 25°C unless otherwise stated. These parameters are for design guidance only and are not tested.

Note 1: Instruction cycle period (TCY) equals four times the input oscillator time base period. All specified values are based on characterization data for that particular oscillator type under standard operating conditions with the device executing code. Exceeding these specified limits may result in an unstable oscillator operation and/or higher than expected current consumption. All devices are tested to operate at "min" values with an external clock applied to OSC1 pin. When an external clock input is used, the "max" cycle time limit is "DC" (no clock) for all devices.

TABLE 16-4:RESET, WATCHDOG TIMER, OSCILLATOR START-UP TIMER, POWER-UP TIMER
AND BROWN-OUT RESET PARAMETERS

Standard Operating Conditions (unless otherwise stated)Operating Temperature $-40^{\circ}C \le TA \le +125^{\circ}C$								
Param No.	Sym	Characteristic	Min	Тур†	Max	Units	Conditions	
30	ТмсL	MCLR Pulse Width (low)	2 5			μS μS	VDD = 5V, -40°C to +85°C VDD = 5V, -40°C to +125°C	
31*	Twdt	Watchdog Timer Time-out Period (No Prescaler)	10 10	20 20	30 35	ms ms	VDD = 5V, -40°C to +85°C VDD = 5V, -40°C to +125°C	
32	Tost	Oscillation Start-up Timer Period ^(1, 2)	_	1024	_	Tosc	(NOTE 3)	
33*	TPWRT	Power-up Timer Period	40	65	140	ms		
34*	Tioz	I/O High-impedance from MCLR Low or Watchdog Timer Reset	_	_	2.0	μS		
35	VBOR	Brown-out Reset Voltage	2.0	2.15	2.3	V	(NOTE 4)	
36*	VHYST	Brown-out Reset Hysteresis	_	100	_	mV		
37*	TBOR	Brown-out Reset Minimum Detection Period	100			μS	$VDD \leq VBOR$	

These parameters are characterized but not tested.

† Data in "Typ" column is at 5V, 25°C unless otherwise stated. These parameters are for design guidance only and are not tested.

- **Note 1:** Instruction cycle period (TCY) equals four times the input oscillator time base period. All specified values are based on characterization data for that particular oscillator type under standard operating conditions with the device executing code. Exceeding these specified limits may result in an unstable oscillator operation and/or higher than expected current consumption. All devices are tested to operate at "min" values with an external clock applied to the OSC1 pin. When an external clock input is used, the "max" cycle time limit is "DC" (no clock) for all devices.
 - 2: By design.
 - **3:** Period of the slower clock.
 - 4: To ensure these voltage tolerances, VDD and Vss must be capacitively decoupled as close to the device as possible. 0.1 μ F and 0.01 μ F values in parallel are recommended.

FIGURE 16-9: PIC12F615/617/HV615 CAPTURE/COMPARE/PWM TIMINGS (ECCP)



TABLE 16-6: PIC12F615/617/HV615 CAPTURE/COMPARE/PWM REQUIREMENTS (ECCP)

Standar Operatir	Standard Operating Conditions (unless otherwise stated) Operating Temperature $-40^{\circ}C \le TA \le +125^{\circ}C$									
Param No.	Sym	Characteristic		Min	Тур†	Max	Units	Conditions		
CC01*	TccL	CCP1 Input Low Time	No Prescaler	0.5Tcy + 20		—	ns			
			With Prescaler	20		_	ns			
CC02*	TccH	CCP1 Input High Time	No Prescaler	0.5Tcy + 20		—	ns			
			With Prescaler	20		—	ns			
CC03*	TccP	CCP1 Input Period		<u>3Tcy + 40</u> N	—	—	ns	N = prescale value (1, 4 or 16)		

These parameters are characterized but not tested.

† Data in "Typ" column is at 5V, 25°C unless otherwise stated. These parameters are for design guidance only and are not tested.

TABLE 16-7: COMPARATOR SPECIFICATIONS

Standard Operating Conditions (unless otherwise stated)Operating Temperature $-40^{\circ}C \le TA \le +125^{\circ}C$								
Param No.	Sym	Characteristics		Min	Тур†	Мах	Units	Comments
CM01	Vos	Input Offset Voltage ⁽²⁾			± 5.0	± 10	mV	
CM02	Vсм	Input Common Mode Voltage		0	—	Vdd - 1.5	V	
CM03*	CMRR	Common Mode Rejection Ratio		+55	—	—	dB	
CM04*	Trt	Response Time ⁽¹⁾	Falling	—	150	600	ns	
			Rising	—	200	1000	ns	
CM05*	TMC2COV	Comparator Mode Change to Output Valid		_	—	10	μS	
CM06*	VHYS	Input Hysteresis Voltage		_	45	60	mV	

These parameters are characterized but not tested.

† Data in "Typ" column is at 5V, 25°C unless otherwise stated. These parameters are for design guidance only and are not tested.

Note 1: Response time is measured with one comparator input at (VDD - 1.5)/2 - 100 mV to (VDD - 1.5)/2 + 20 mV. The other input is at (VDD -1.5)/2.

2: Input offset voltage is measured with one comparator input at (VDD - 1.5V)/2.

Param	Device Characteristics	Units	Min	Тур	Max	Condition		
No.					Max	Vdd	Note	
D010				13	58	2.0		
	Supply Current (IDD)	μA		19	67	3.0	IDD LP OSC (32 kHz)	
			_	32	92	5.0		
D011			_	135	316	2.0		
		μΑ		185	400	3.0	IDD XT OSC (1 MHz)	
				300	537	5.0		
D012			_	240	495	2.0		
		μΑ	_	360	680	3.0	IDD XT OSC (4 MHz)	
		mA	_	0.660	1.20	5.0		
D013			_	75	158	2.0	IDD EC OSC (1 MHz)	
		μΑ	_	155	338	3.0		
			_	345	792	5.0		
D014			_	185	357	2.0	IDD EC OSC (4 MHz)	
		μΛ	_	325	625	3.0		
		mA	_	0.665	1.30	5.0		
D016			_	245	476	2.0	IDD INTOSC (4 MHz)	
		μΑ	_	360	672	3.0		
			_	620	1.10	5.0		
D017		μA	_	395	757	2.0	IDD INTOSC (8 MHz)	
			_	0.620	1.20	3.0		
			_	1.20	2.20	5.0		
D018			_	175	332	2.0	IDD EXTRC (4 MHz)	
		μA	_	285	518	3.0		
				530	972	5.0		
D019		m۸	—	2.20	4.10	4.5		
			_	2.80	4.80	5.0		

TABLE 16-14: DC CHARACTERISTICS FOR IDD SPECIFICATIONS FOR PIC12F615-H (High Temp.)

17.0 DC AND AC CHARACTERISTICS GRAPHS AND TABLES

Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore, outside the warranted range.

"Typical" represents the mean of the distribution at 25°C. "Maximum" or "minimum" represents (mean + 3σ) or (mean - 3σ) respectively, where s is a standard deviation, over each temperature range.









FIGURE 17-48: 1.2V REFERENCE VOLTAGE vs. TEMP (TYPICAL)



FIGURE 17-49: SHUNT REGULATOR VOLTAGE vs. INPUT CURRENT (TYPICAL)



APPENDIX A: DATA SHEET REVISION HISTORY

Revision A

This is a new data sheet.

Revision B (05/2008)

Added Graphs. Revised 28-Pin ICD Pinout, Electrical Specifications Section, Package Details.

Revision C (09/2009)

Updated adding the PIC12F617 device throughout the entire data sheet; Added Figure 2-2 to Memory Organization section; Added section 3 "FLASH PROGRAM MEMORY SELF READ/SELF WRITE CONTROL (FOR PIC12F617 ONLY)"; Updated Register 12-1; Updated Table12-5 adding PMCON1, PMCON2, PMADRL, PMADRH, PMDATL, PMDATH; Added section 16-12 in the Electrical Specification section; Other minor edits.

Revision D (01/2010)

Updated Figure 17-50; Revised 16.8 DC Characteristics; Removed Preliminary Status.

APPENDIX B: MIGRATING FROM OTHER PIC® DEVICES

This discusses some of the issues in migrating from other PIC devices to the PIC12F6XX Family of devices.

B.1 PIC12F675 to PIC12F609/615/ 12HV609/615

TABLE B-1:	FEATURE	COMPARISON
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Feature	PIC12F675	PIC12F609/ 615/ 12HV609/615		
Max Operating Speed	20 MHz	20 MHz		
Max Program Memory (Words)	1024	1024		
SRAM (bytes)	64	64		
A/D Resolution	10-bit	10-bit (615 only)		
Timers (8/16-bit)	1/1	2/1 (615) 1/1 (609)		
Oscillator Modes	8	8		
Brown-out Reset	Y	Y		
Internal Pull-ups	RA0/1/2/4/5	GP <u>0/1/2/4</u> /5, MCLR		
Interrupt-on-change	RA0/1/2/3/4/5	GP0/1/2/3/4/5		
Comparator	1	1		
ECCP	N	Y (615)		
INTOSC Frequencies	4 MHz	4/8 MHz		
Internal Shunt Regulator	Ν	Y (PIC12HV609/ 615)		

Note: This device has been designed to perform to the parameters of its data sheet. It has been tested to an electrical specification designed to determine its conformance with these parameters. Due to process differences in the manufacture of this device, this device may have different performance characteristics than its earlier version. These differences may cause this device to perform differently in your application than the earlier version of this device.